



SMD Schottky Barrier Diode

RB751G40-G (RoHS Device)

Reverse Voltage: 30 Volts

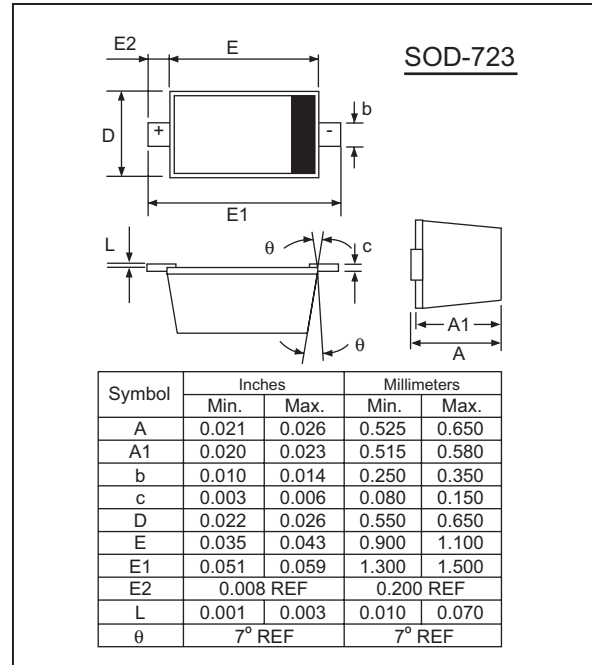
Forward Current: 30 mA

Features:

- Small Surface Mounting Type
- High Reliability
- Low Reverse Current and Low Forward Voltage

Mechanical Data:

- Case: Molded plastic SOD-723
- Terminals: Solderable per MIL-STD-750, Method 2026.1.
- Polarity: Indicated by cathode band.
- Mounting position: Any.
- Marking: F



Maximum Ratings (at $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	30	mA
Peak forward surge current	I_{FSM}	200	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40~+125	$^\circ\text{C}$

Electrical Ratings (at $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F			0.37	V	$I_F=1\text{mA}$
Reverse current	I_R			0.5	μA	$V_R=30\text{V}$
Capacitance between terminals	C_T		2		pF	$V_R=1\text{V}$, $f=1\text{MHz}$

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Electrical Characteristic Curves

Fig. 1 Forward Characteristics

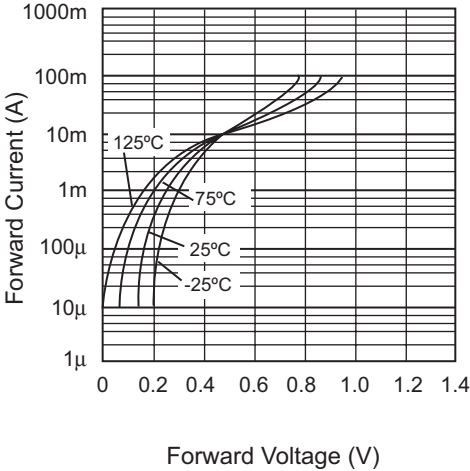


Fig. 2 Reverse Characteristics

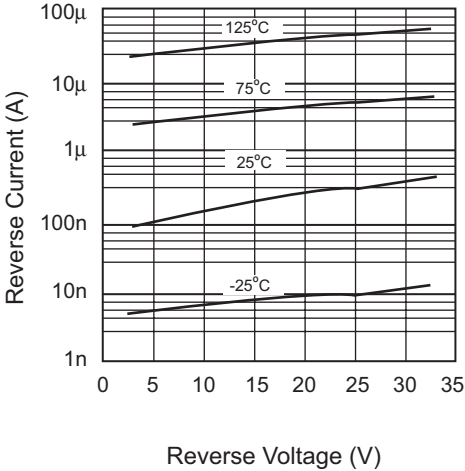
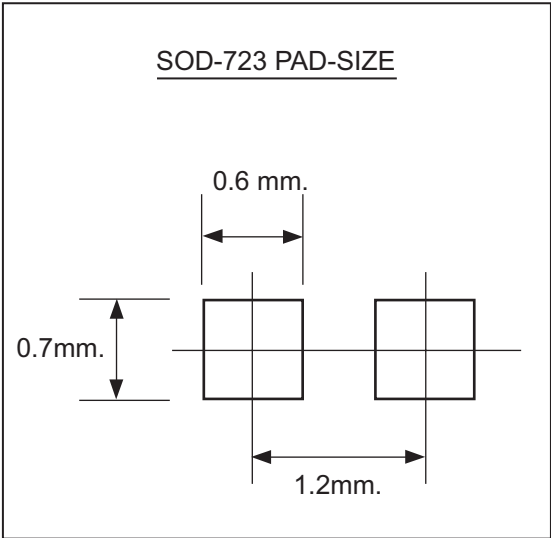
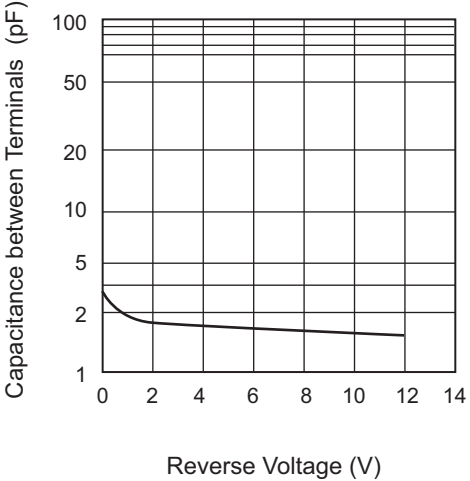


Fig. 3 Capacitance between Terminals



"-G" suffix designated RoHS compliant version